

EPITAXIAL GROWTH METHOD OF SEMICONDUCTOR

ABSTRACT OF THE DISCLOSURE

An epitaxial growth method of semiconductor can reliably avoid irregularities from being produced when a II-VI compound semiconductor is grown epitaxially. When this method is applied to a method of manufacturing a semiconductor light-emitting device, it is possible to obtain a semiconductor light-emitting device having a long life and excellent light-emitting characteristic. When a II-VI compound semiconductor is grown epitaxially, a VI/II ratio, i.e., a supplying ratio of VI-group element and II-group element used in the epitaxial growth is selected in a range of from 1.3 to 2.5

Figure 1